

# Minhao Zhang

## List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Intrinsic magnetic topological insulator phases in the Sb doped MnBi <sub>2</sub> Te <sub>4</sub> bulks and thin flakes. Nature Communications, 2019, 10, 4469.	12.8	212
2	Evidence of Both Surface and Bulk Dirac Bands and Anisotropic Nonsaturating Magnetoresistance in ZrSiS. Advanced Electronic Materials, 2016, 2, 1600228.	5.1	115
3	Nontopological origin of the planar Hall effect in the type-II Dirac semimetal $\text{NiTe}_2$ . Physical Review B, 2019, 99, .		
4	A Gd@C <sub>82</sub> single-molecule electret. Nature Nanotechnology, 2020, 15, 1019-1024.	31.5	70
5	Experimental Observation of the Gate-Controlled Reversal of the Anomalous Hall Effect in the Intrinsic Magnetic Topological Insulator MnBi <sub>2</sub> Te <sub>4</sub> Device. Nano Letters, 2020, 20, 709-714.	9.1	60
6	Band Structure Perfection and Superconductivity in Type-II Dirac Semimetal $\text{IrPtTe}_2$ . Advanced Materials, 2018, 30, e1801556.	21.0	47
7	Inclined Ultrathin Bi <sub>2</sub> O <sub>2</sub> Se Films: A Building Block for Functional van der Waals Heterostructures. ACS Nano, 2020, 14, 16803-16812.	14.6	45
8	Tuning the transport behavior of centimeter-scale WTe <sub>2</sub> ultrathin films fabricated by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	3.3	34
9	Transport evidence of 3D topological nodal-line semimetal phase in ZrSiS. Frontiers of Physics, 2018, 13, 1.	5.0	30
10	Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO <sub>3</sub> Epitaxial Thin Film System. Advanced Electronic Materials, 2018, 4, 1800055.	5.1	27
11	Ultrahigh Hall mobility and suppressed backward scattering in layered semiconductor Bi <sub>2</sub> O <sub>2</sub> Se. Applied Physics Letters, 2018, 113, .	3.3	27
12	Controllable synthesis and magnetotransport properties of Cd <sub>3</sub> As <sub>2</sub> Dirac semimetal nanostructures. RSC Advances, 2017, 7, 17689-17696.	3.6	21
13	The Material Efforts for Quantized Hall Devices Based on Topological Insulators. Advanced Materials, 2020, 32, e1904593.	21.0	19
14	Intrinsic ferromagnetism and quantum transport transition in individual Fe-doped Bi <sub>2</sub> Se <sub>3</sub> topological insulator nanowires. Nanoscale, 2017, 9, 12372-12378.	5.6	18
15	The mechanism exploration for zero-field ferromagnetism in intrinsic topological insulator MnBi <sub>2</sub> Te <sub>4</sub> by Bi <sub>2</sub> Te <sub>3</sub> intercalations. Applied Physics Letters, 2020, 116, 221902.	3.3	17
16	Magneto-transport and Shubnikov-de Haas oscillations in the layered ternary telluride topological semimetal candidate Ta <sub>3</sub> SiTe <sub>6</sub> . Applied Physics Letters, 2020, 116, .	3.3	15
17	Experimental evidence for dissipationless transport of the chiral edge state of the high-field Chern insulator in $\text{MnBi}_2\text{Te}_4$ nanodevices. Physical Review B, 2022, 105, .	3.2	15
18	Topological Phase Transition-Induced Triaxial Vector Magnetoresistance in $(\text{BiIn})_2\text{Se}_3$ Nanodevices. ACS Nano, 2018, 12, 1537-1543.	14.6	13

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19	Transition and anomalous scaling in the quantum Hall transport of topological-insulator $B_i \nu$ $\nu > 1.1$	3.2	13
20	Layered Topological Insulators and Semimetals for Magneto-resistance Type Sensors. Advanced Quantum Technologies, 2019, 2, 1800039.	3.9	10
21	The Unique Current-Direction Dependent On-Off Switching in BiSbTeSe <sub>2</sub> Topological Insulator Based Spin Valve Transistors. IEEE Electron Device Letters, 2016, , 1-1.	3.9	7
22	Unconventional anomalous Hall effect in magnetic topological insulator MnBi <sub>4</sub> Te <sub>7</sub> device. Applied Physics Letters, 2021, 118, .	3.3	7
23	Room-temperature ferromagnetism observed in Nd-doped In <sub>2</sub> O <sub>3</sub> dilute magnetic semiconducting nanowires. Chinese Physics B, 2016, 25, 097502.	1.4	4
24	Quantum oscillations and nontrivial transport in (Bi <sub>0.92</sub> In <sub>0.08</sub> ) <sub>2</sub> Se <sub>3</sub> . Chinese Physics B, 2017, 26, 127305.	1.4	4
25	Electrical spin polarization through spin-momentum locking in topological-insulator nanostructures. Chinese Physics B, 2018, 27, 097307.	1.4	4
26	Quantum Electronics: Evidence of Both Surface and Bulk Dirac Bands and Anisotropic Nonsaturating Magneto-resistance in ZrSiS (Adv. Electron. Mater. 10/2016). Advanced Electronic Materials, 2016, 2, .	5.1	3
27	Emergent Ferromagnetism: Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO <sub>3</sub> Epitaxial Thin Film System (Adv. Electron. Mater. 6/2018). Advanced Electronic Materials, 2018, 4, 1870030.	5.1	1
28	Effect of Superparamagnetic Fe <sub>3</sub> O <sub>4</sub> Nanoparticles on Schottky Barriers of Graphene. IEEE Transactions on Magnetics, 2015, 51, 1-4.	2.1	0
29	Layered topological semimetals for spintronics. , 2020, , 273-298.		0